

**Numerical study of current crowding phenomenon in complementary 4H-SiC JBS rectifiers**

**Rang, Toomas; Higelin, G.; Kurel, Raido** Silicon Carbide and Related Materials 2003 2004 / p. 1045-1048

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**The basic parameters of diffusion welded Al Schottky contacts to p- and n-SiC**

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